

SM Series 400W TVS Diode Array



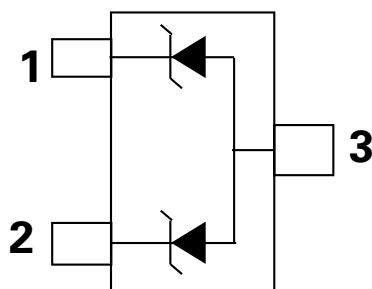
Description

The SM series TVS Diode Array is designed to protect sensitive equipment from damage due to electrostatic discharge (ESD), electrical fast transients (EFT), and lightning induced surges.

The SM series can absorb repetitive ESD strikes above the maximum level specified in the IEC61000-4-2 international standard without performance degradation and safely dissipate up to 24A of 8/20us induced surge current (IEC-61000-4-5) with very low clamping voltages.

Pinout and Functional Block Diagram

(AEC-Q101 qualified)



Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

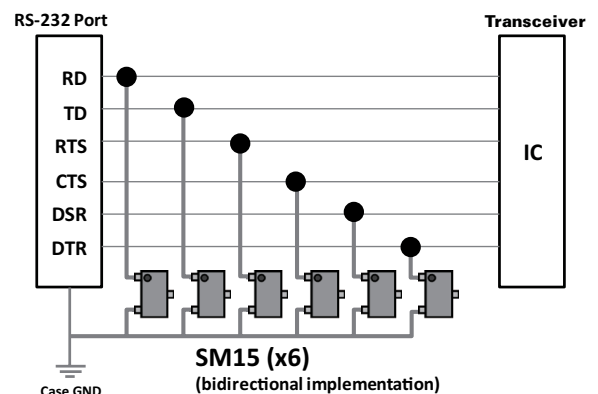
Features

- ESD, IEC61000-4-2, $\pm 30\text{kV}$ contact, $\pm 30\text{kV}$ air
- EFT, IEC61000-4-4, 50A (5/50ns)
- Lightning, IEC61000-4-5, 24A ($t_p=8/20\mu\text{s}$, SM05)
- Working voltages: 5V, 12V, 15V, 24V and 36V
- Low clamping voltage
- Low leakage current
- AEC-Q101 qualified (SOT23-3 package)

Applications

- Industrial Equipment
- Test and Medical Equipment
- Point-of-Sale Terminals
- Motor Controls
- Legacy Ports (RS-232, RS-485)
- Security and Alarm Systems

RS-232 Application Example



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
P_{PK}	Peak Pulse Power ($t_p=8/20\mu s$)	400	W
T_{OP}	Operating Temperature	-40 to 125	°C
T_{STOR}	Storage Temperature	-55 to 150	°C

Notes:

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Thermal Information

Parameter	Rating	Units
Storage Temperature Range	-55 to 150	°C
Maximum Junction Temperature	150	°C
Maximum Lead Temperature (Soldering 20-40s)	260	°C

SM05 Electrical Characteristics ($T_{OP}=25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R \leq 1\mu A$			5.0	V
Reverse Voltage Drop	V_R	$I_R = 1mA$	6.0			V
Leakage Current	I_{LEAK}	$V_R = 5V$			1.0	μA
Clamp Voltage ¹	V_C	$I_{PP}=1A, t_p=8/20\mu s$, Pin 1 or Pin 2 to Pin 3			9.8	V
		$I_{PP}=10A, t_p=8/20\mu s$, Pin 1 or Pin 2 to Pin 3			13.0	V
Dynamic Resistance ²	R_{DYN}	TLP, $t_p=100ns$, I/O to GND		0.19		Ω
Peak Pulse Current (8/20 μs) ¹	I_{PP}	$t_p=8/20\mu s$			24.0	A
ESD Withstand Voltage ¹	V_{ESD}	IEC61000-4-2 (Contact Discharge)	± 30			kV
		IEC61000-4-2 (Air Discharge)	± 30			kV
Diode Capacitance ¹	$C_{I/O-GND}$	Reverse Bias=0V, f=1MHz			400	pF
	$C_{I/O-I/O}$	Reverse Bias=0V, f=1MHz			350	pF

SM12 Electrical Characteristics ($T_{OP}=25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R \leq 1\mu A$			12.0	V
Reverse Voltage Drop	V_R	$I_R = 1mA$	13.3			V
Leakage Current	I_{LEAK}	$V_R = 12V$			1.0	μA
Clamp Voltage ¹	V_C	$I_{PP}=1A, t_p=8/20\mu s$, Pin 1 or Pin 2 to Pin 3			18.5	V
		$I_{PP}=10A, t_p=8/20\mu s$, Pin 1 or Pin 2 to Pin 3			22.5	V
Dynamic Resistance ²	R_{DYN}	TLP, $t_p=100ns$, I/O to GND		0.25		Ω
Peak Pulse Current (8/20 μs) ¹	I_{PP}	$t_p=8/20\mu s$			17.0	A
ESD Withstand Voltage ¹	V_{ESD}	IEC61000-4-2 (Contact Discharge)	± 30			kV
		IEC61000-4-2 (Air Discharge)	± 30			kV
Diode Capacitance ¹	$C_{I/O-GND}$	Reverse Bias=0V, f=1MHz			150	pF
	$C_{I/O-I/O}$	Reverse Bias=0V, f=1MHz			120	pF

SM15 Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1 μA			15.0	V
Reverse Voltage Drop	V _R	I _R = 1 mA	16.7			V
Leakage Current	I _{LEAK}	V _R = 15V			1.0	μA
Clamp Voltage ¹	V _C	I _{PP} = 1A, t _p = 8/20μs, Pin 1 or Pin 2 to Pin 3			24.0	V
		I _{PP} = 10A, t _p = 8/20μs, Pin 1 or Pin 2 to Pin 3			30.0	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p = 100ns, I/O to GND		0.30		Ω
Peak Pulse Current (8/20μs) ¹	I _{PP}	t _p = 8/20μs			12.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Contact Discharge)	±30			kV
		IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias=0V, f=1MHz			100	pF
	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz			75	pF

SM24 Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1 μA			24.0	V
Reverse Voltage Drop	V _R	I _R = 1 mA	26.7			V
Leakage Current	I _{LEAK}	V _R = 24V			1.0	μA
Clamp Voltage ¹	V _C	I _{PP} = 1A, t _p = 8/20μs, Pin 1 or Pin 2 to Pin 3			36.0	V
		I _{PP} = 5A, t _p = 8/20μs, Pin 1 or Pin 2 to Pin 3			42.0	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p = 100ns, I/O to GND		0.50		Ω
Peak Pulse Current (8/20μs) ¹	I _{PP}	t _p = 8/20μs			7.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Contact Discharge)	±30			kV
		IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias=0V, f=1MHz			65	pF
	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz			50	pF

SM36 Electrical Characteristics (T_{OP}=25°C)

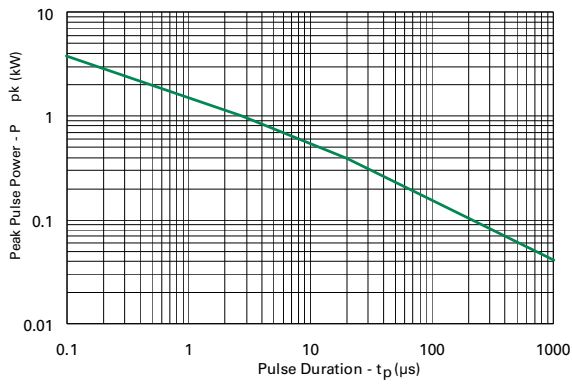
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1 μA			36.0	V
Reverse Voltage Drop	V _R	I _R = 1 mA	40.0			V
Leakage Current	I _{LEAK}	V _R = 36V			1.0	μA
Clamp Voltage ¹	V _C	I _{PP} = 1A, t _p = 8/20μs, Pin 1 or Pin 2 to Pin 3			52.0	V
		I _{PP} = 4A, t _p = 8/20μs, Pin 1 or Pin 2 to Pin 3			62.0	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p = 100ns, I/O to GND		0.65		Ω
Peak Pulse Current (8/20μs) ¹	I _{PP}	t _p = 8/20μs			5.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Contact Discharge)	±30			kV
		IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias=0V, f=1MHz			50	pF
	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz			40	pF

Note:

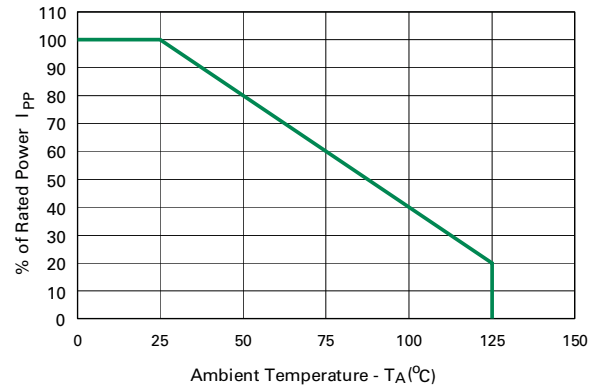
¹ Parameter is guaranteed by design and/or device characterization.

² Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.

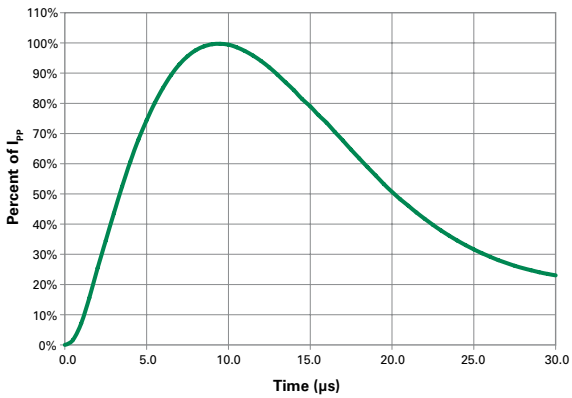
Non-Repetitive Peak Pulse Power vs. Pulse Time



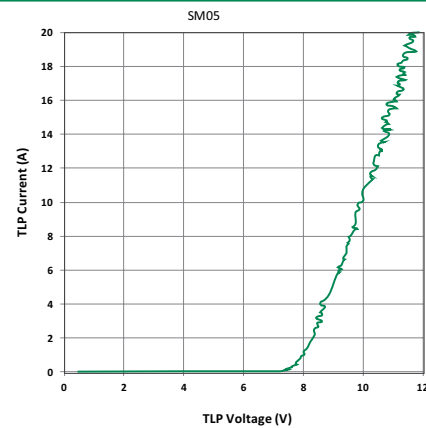
Power Derating Curve



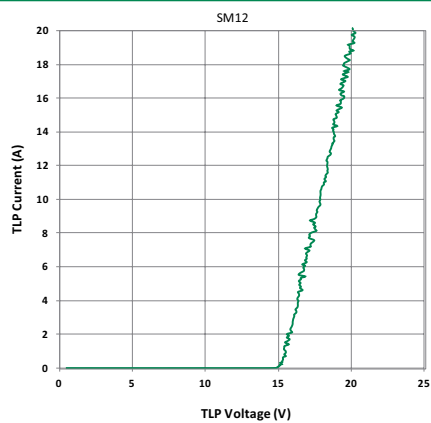
Pulse Waveform



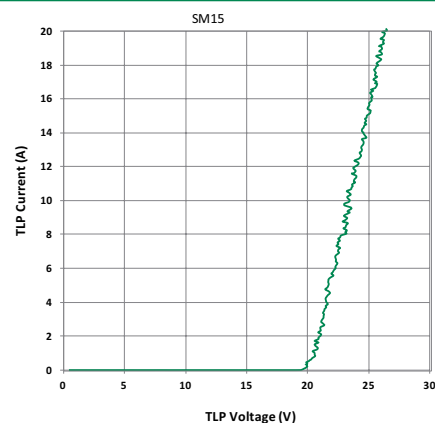
SM05 Transmission Line Pulsing(TLP) Plot



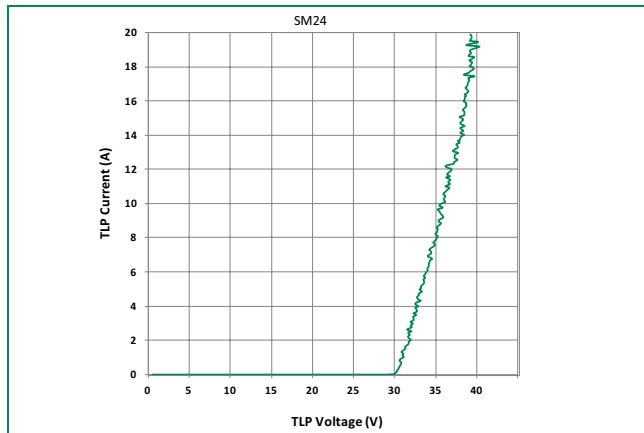
SM12 Transmission Line Pulsing(TLP) Plot



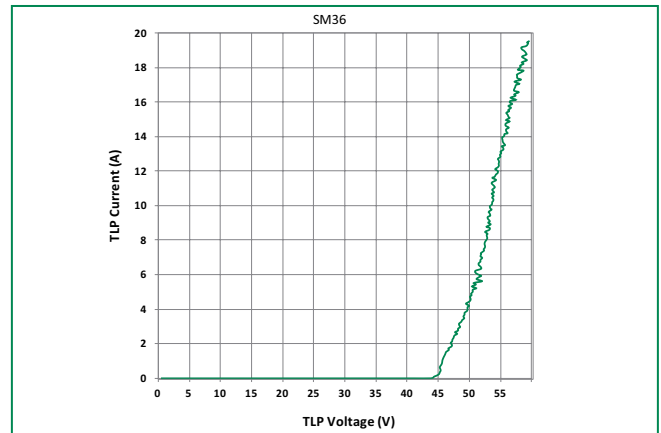
SM15 Transmission Line Pulsing(TLP) Plot



SM24 Transmission Line Pulsing (TLP) Plot

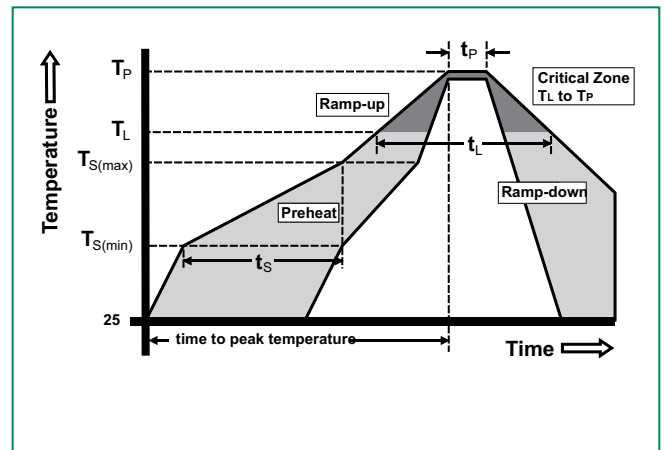


SM36 Transmission Line Pulsing (TLP) Plot



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak		3°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		260°C



Ordering Information

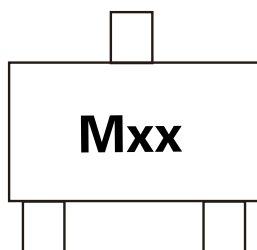
Part Number	Package	Marking	Min. Order Qty.
SM05-02HTG	SOT23-3	M05	3000
SM12-02HTG	SOT23-3	M12	3000
SM15-02HTG	SOT23-3	M15	3000
SM24-02HTG	SOT23-3	M24	3000
SM36-02HTG	SOT23-3	M36	3000

Product Characteristics

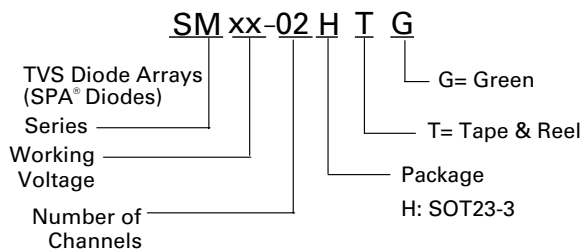
Lead Plating	Matte Tin
Lead Material	Copper Alloy
Lead Coplanarity	0.0004 inches (0.102mm)
Substitute Material	Silicon
Body Material	Molded Epoxy
Flammability	UL 94 V-0

- Notes :
1. All dimensions are in millimeters.
 2. Dimensions include solder plating.
 3. Dimensions are exclusive of mold flash & metal burr.
 4. Bld is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
 5. Package surface matte finish VDI 11-13.

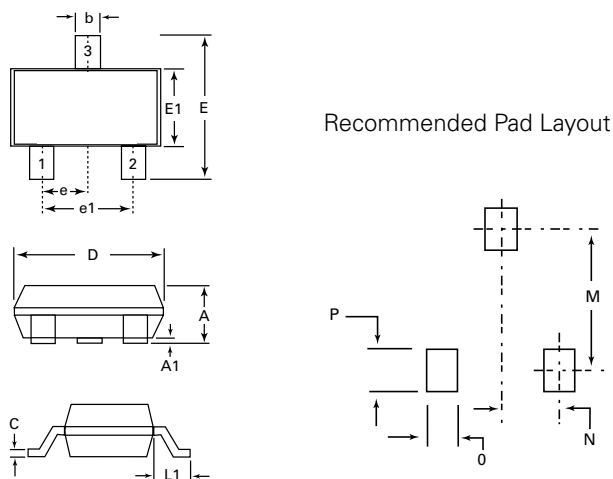
Part Marking System



Part Numbering System

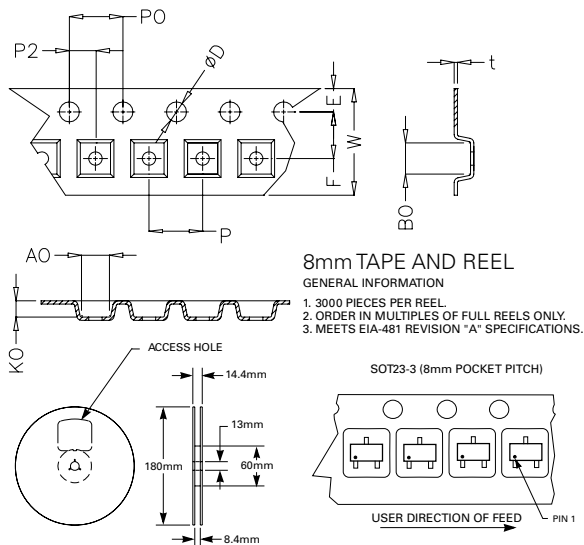


Package Dimensions — SOT23-3



Package	SOT23-3			
Pins	3			
JEDEC	TO-236			
	Millimeters		Inches	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A1	0.01	0.1	0.0004	0.004
b	0.3	0.5	0.012	0.020
c	0.08	0.2	0.003	0.008
D	2.8	3.04	0.110	0.120
E	2.1	2.64	0.083	0.104
E1	1.2	1.4	0.047	0.055
e	0.95 BSC		0.038 BSC	
e1	1.90 BSC		0.075 BSC	
L1	0.54 REF		0.021 REF	
M		2.29		.090
N		0.95		0.038
O		0.78		.030TYP
P		0.78		.030TYP

Embossed Carrier Tape & Reel Specification — SOT23-3



Symbol	Millimetres		Inches	
	Min	Max	Min	Max
E	1.65	1.85	0.065	0.073
F	3.40	3.60	0.134	0.142
P2	1.90	2.10	0.075	0.083
D	1.40	1.60	0.055	0.063
P0	3.90	4.10	0.154	0.161
W	7.70	8.30	0.303	0.327
P	3.90	4.10	0.154	0.161
A0	3.05	3.25	0.120	0.128
B0	2.67	2.87	0.105	0.113
K0	1.12	1.32	0.044	0.052
t	0.22	0.24	0.009	0.009



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- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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